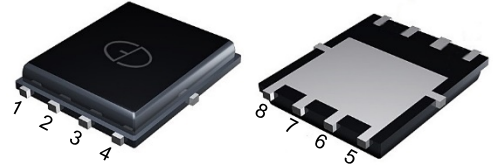


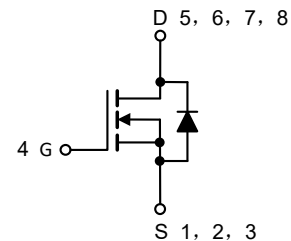
## N-Channel 60V (D-S) Power MOSFET

### Features

- 100% Avalanche Tested
- Extremely Low Losses with Low FOM  $R_{DS(on)} \cdot Q_g$
- Halogen Free, Pb-Free
- RoHS Compliant



PDFN5060



### Applications

- DC-DC
- Motors, lamps
- Power switching

### Absolute Maximum Ratings ( $T_J=25^\circ\text{C}$ unless otherwise noted)

| Parameter                                        | Symbol          | Value                         | Unit             |
|--------------------------------------------------|-----------------|-------------------------------|------------------|
| Drain Source Voltage                             | $V_{DS}$        | 60                            | V                |
| Gate Source Voltage                              | $V_{GS}$        | $\pm 20$                      | V                |
| Drain Current, Continuous<br>$V_{GS}=10\text{V}$ | $I_D$           | $T_C=25^\circ\text{C}$<br>143 | A                |
|                                                  |                 | $T_C=100^\circ\text{C}$<br>90 |                  |
| Drain Current, Pulsed (Note 1)                   | $I_{DM}$        | 541                           | A                |
| Single Avalanche Energy (Note 2)                 | $E_{AS}$        | 314                           | mJ               |
| Power Dissipation                                | $P_D$           | $T_C=25^\circ\text{C}$<br>104 | W                |
|                                                  |                 | $T_C=100^\circ\text{C}$<br>42 |                  |
| Operating Junction/ Storage Temperature Range    | $T_J / T_{STG}$ | -55 to +150                   | $^\circ\text{C}$ |

Note 1: Single pulse;  $t_p \leq 1\text{us}$ .

Note 2:  $V_{DD} = 30\text{V}$ ,  $V_{GS} = 10\text{V}$ ,  $L = 1\text{mH}$ ,  $R_G = 25\Omega$ , starting  $T_J = 25^\circ\text{C}$ .

### Thermal Characteristics

| Parameter                                       | Symbol     | Max | Unit               |
|-------------------------------------------------|------------|-----|--------------------|
| Thermal Resistance Junction to Case             | $R_{thJC}$ | 1.2 | $^\circ\text{C/W}$ |
| Thermal Resistance Junction to Ambient (Note 3) | $R_{thJA}$ | 45  | $^\circ\text{C/W}$ |

Note 3: Device mounted on 1 square inch FR4 PCB board, with 2oz single-sided copper, in a  $25^\circ\text{C}$  still air environment.

## Electrical Characteristics (T<sub>J</sub> = 25°C unless otherwise noted)

| Parameter                                 | Symbol               | Test Conditions                                                                               | Min | Typ  | Max  | Unit |
|-------------------------------------------|----------------------|-----------------------------------------------------------------------------------------------|-----|------|------|------|
| Drain-Source Breakdown Voltage            | V <sub>(BR)DSS</sub> | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA                                                    | 60  | --   | --   | V    |
| Zero Gate Voltage Drain Current           | I <sub>DSS</sub>     | V <sub>DS</sub> =60V, V <sub>GS</sub> =0V                                                     | --  | --   | 1.0  | uA   |
| Gate Threshold Voltage                    | V <sub>GS(TH)</sub>  | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250uA                                     | 1.2 | 1.7  | 2.5  | V    |
| Gate Leakage Current                      | I <sub>GSS</sub>     | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V                                                    | --  | --   | ±100 | nA   |
| Drain-Source On-state Resistance (Note 4) | R <sub>DS(on)</sub>  | V <sub>GS</sub> =10V, I <sub>D</sub> =20A                                                     | --  | 2.4  | 2.9  | mΩ   |
|                                           |                      | V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A                                                    | --  | 3.4  | 4.1  |      |
| Total Gate Charge                         | Q <sub>g</sub>       | V <sub>GS(off)</sub> =0V, V <sub>GS(on)</sub> =10V, V <sub>DD</sub> =30V, I <sub>D</sub> =20A | --  | 42   | --   | nC   |
| Gate-Source Charge                        | Q <sub>gs</sub>      |                                                                                               | --  | 6.6  | --   |      |
| Gate-Drain Charge                         | Q <sub>gd</sub>      |                                                                                               | --  | 9.3  | --   |      |
| Turn-on Delay Time                        | t <sub>d(on)</sub>   | V <sub>GS</sub> =10V, V <sub>DD</sub> =30V, I <sub>D</sub> =20A, R <sub>G</sub> =3Ω           | --  | 4.5  | --   | ns   |
| Turn-on Rise Time                         | t <sub>r</sub>       |                                                                                               | --  | 5    | --   |      |
| Turn-off Delay Time                       | t <sub>d(off)</sub>  |                                                                                               | --  | 32   | --   |      |
| Turn-off Fall Time                        | t <sub>f</sub>       |                                                                                               | --  | 16   | --   |      |
| Gate Resistance                           | R <sub>g</sub>       | V <sub>GS</sub> =0V, f=1MHz, open drain                                                       | --  | 1.2  | --   | Ω    |
| Input Capacitance                         | C <sub>iss</sub>     | V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, f=1MHz                                             | --  | 2376 | --   | pF   |
| Output Capacitance                        | C <sub>oss</sub>     |                                                                                               | --  | 1153 | --   |      |
| Reverse Transfer Capacitance              | C <sub>rss</sub>     |                                                                                               | --  | 58   | --   |      |

## Reverse Diode Characteristics (T<sub>J</sub> = 25°C unless otherwise noted)

| Parameter                      | Symbol          | Test Conditions                         | Min | Typ | Max | Unit |
|--------------------------------|-----------------|-----------------------------------------|-----|-----|-----|------|
| Forward Current, Continuous    | I <sub>SD</sub> | T <sub>C</sub> =25°C                    | --  | --  | 143 | A    |
| Diode Forward Voltage (Note 4) | V <sub>SD</sub> | I <sub>F</sub> =2A, V <sub>GS</sub> =0V | --  | 0.7 | 1.2 | V    |
| Reverse Recovery Time          | T <sub>rr</sub> | I <sub>F</sub> = 20A, di/dt = 100 A/μs  | --  | 44  | --  | ns   |
| Reverse Recovery Charge        | Q <sub>rr</sub> |                                         | --  | 38  | --  | nC   |

Note 4: Pulse test; pulse width ≤ 380μs, duty cycle ≤ 1%.

## Typical Characteristics Curves ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Fig1 - Output Characteristics

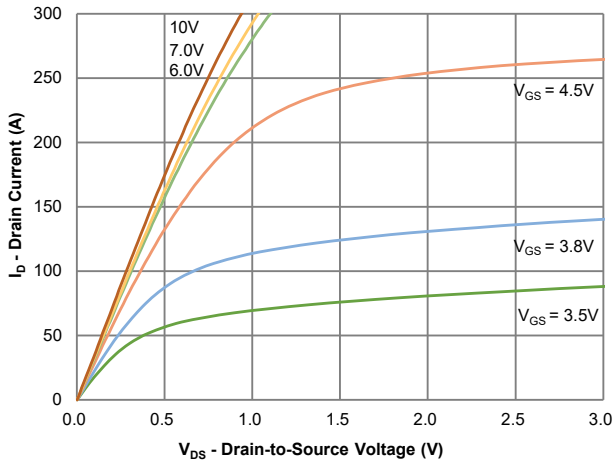


Fig2 - Transfer Characteristics

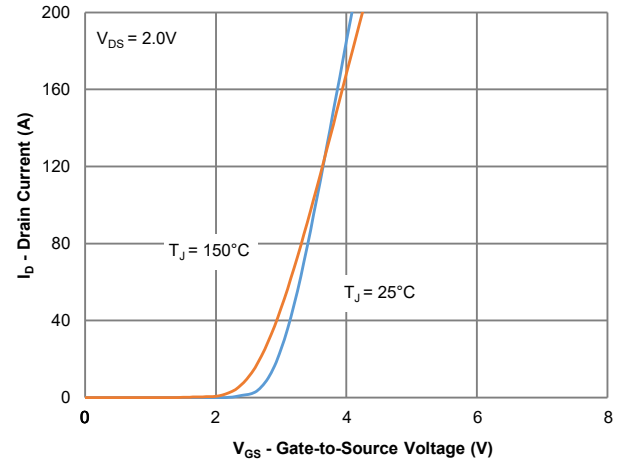


Fig3 - On-Resistance vs. Gate-Source Voltage

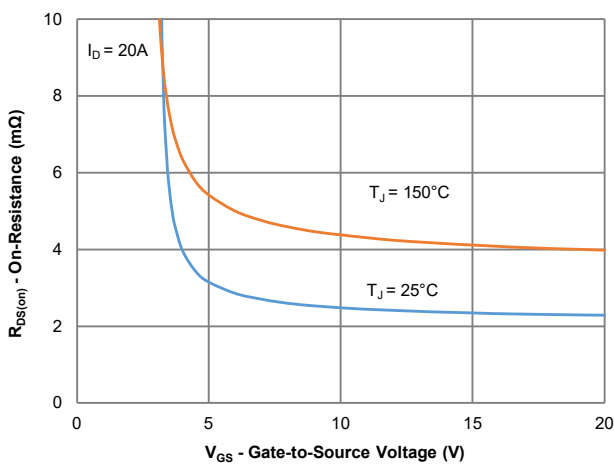


Fig4 - On-Resistance vs. Drain Current and Gate Voltage

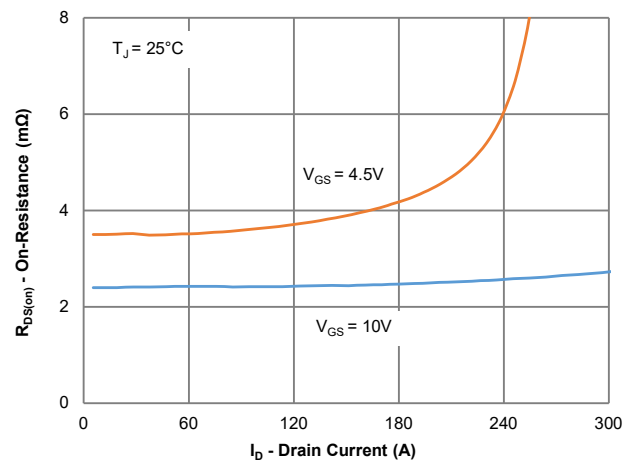


Fig5 - On-Resistance vs. Junction Temperature

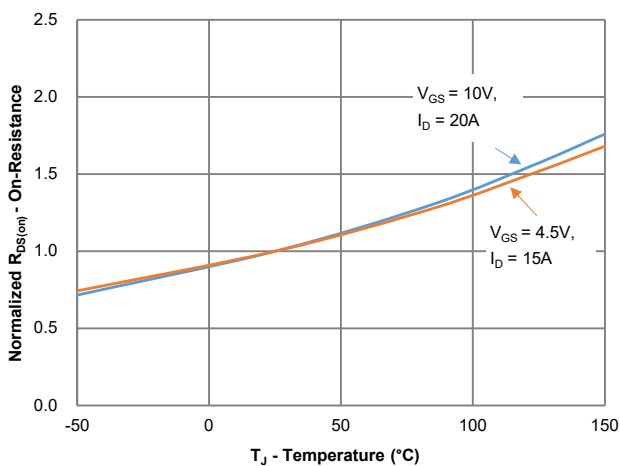
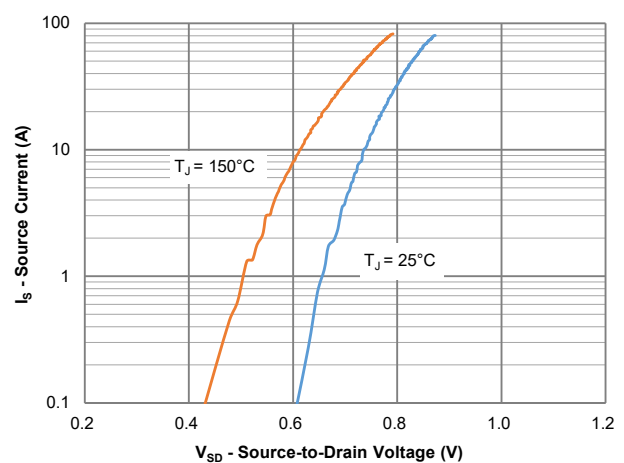


Fig6 - Source-Drain Diode Forward Voltage



## Typical Characteristics Curves ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Fig7 - Gate Threshold Variation vs. Junction Temperature

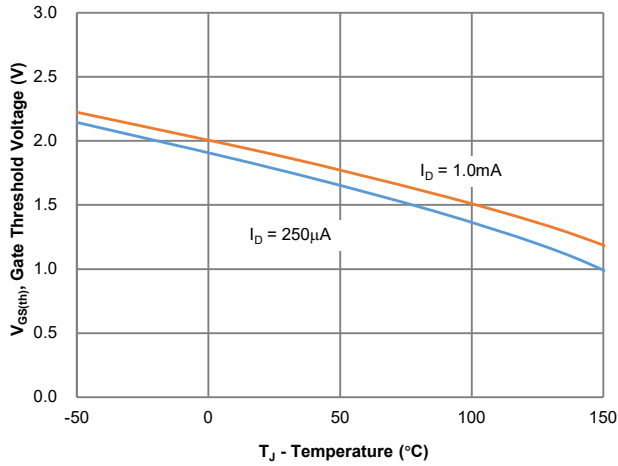


Fig8 - Gate Charge Characteristics

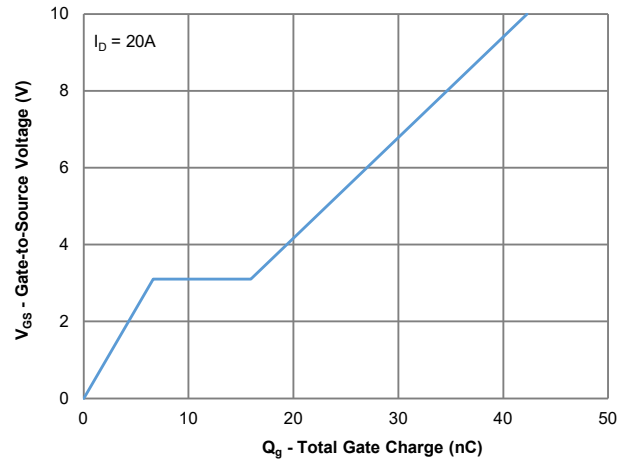


Fig9 - Capacitance Characteristics

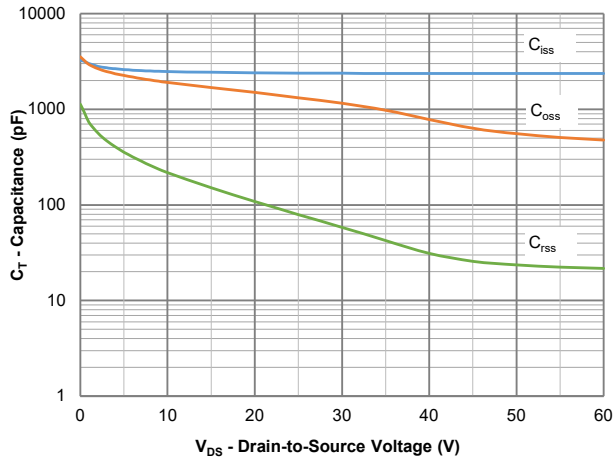


Fig10 - Power Derating

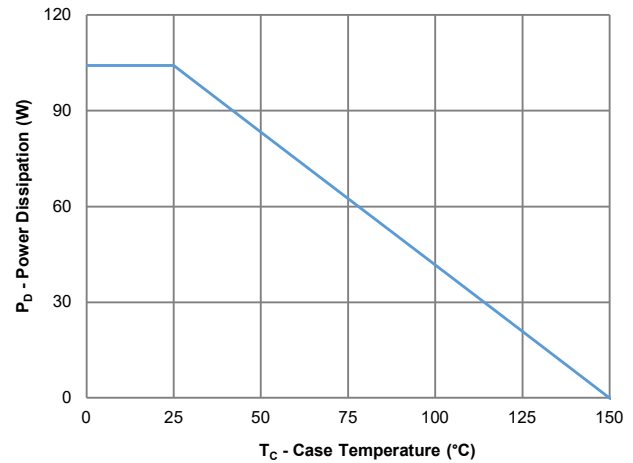


Fig11 - Current Derating

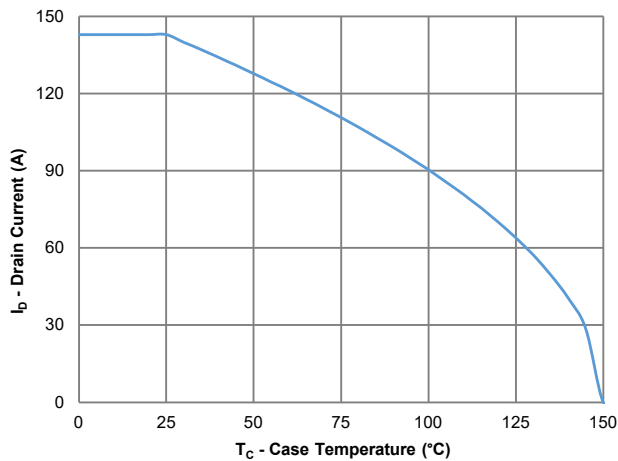
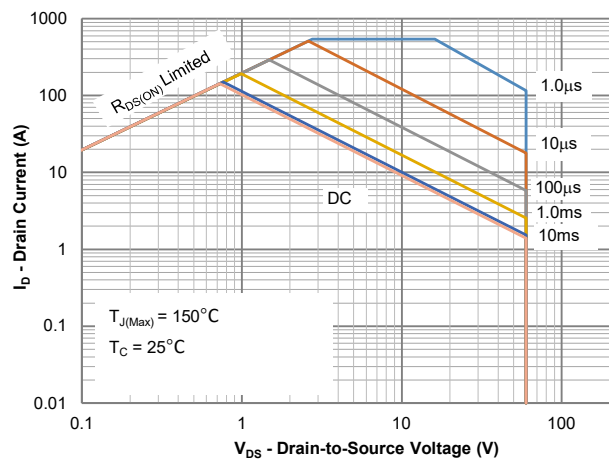
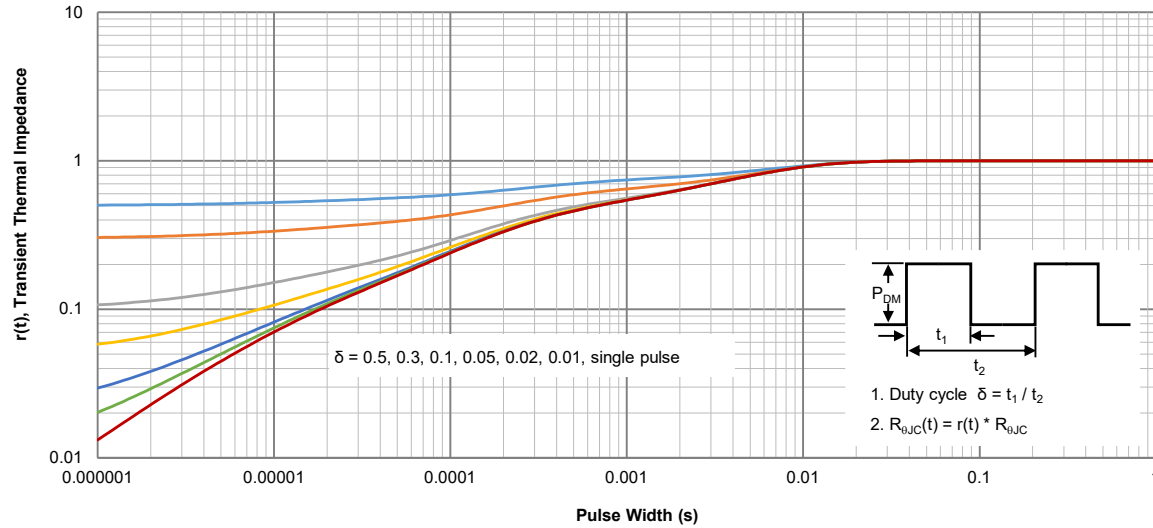


Fig12 - Safe Operating Area



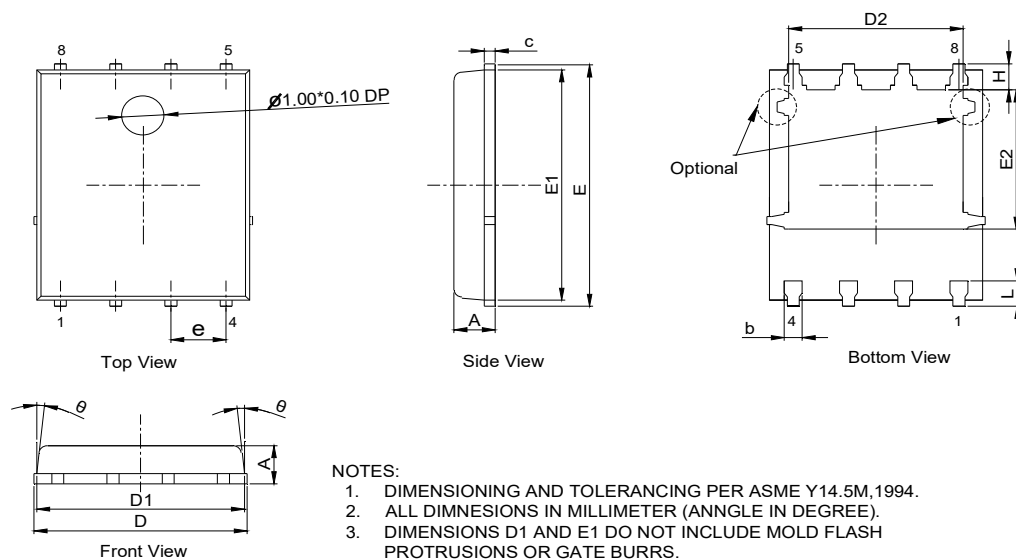
## Typical Characteristics Curves (T<sub>J</sub> = 25°C unless otherwise noted)

Fig13 - Normalized Maximum Transient Thermal Impedance



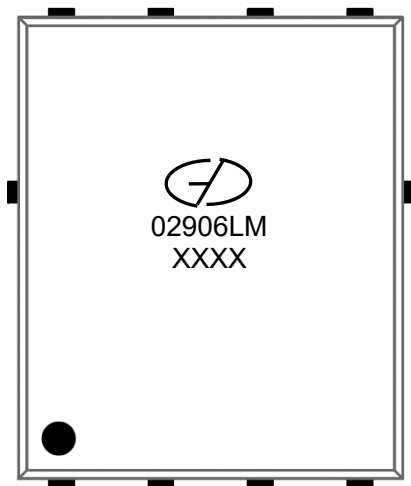
## Package Outline Dimensions (Unit: millimeters)

### PDFN5060



| DIM.     | MILLIMETER |      |      |
|----------|------------|------|------|
|          | MIN.       | NOM. | MAX. |
| A        | 0.90       | 1.00 | 1.10 |
| b        | 0.20       | —    | 0.51 |
| c        | 0.21       | 0.25 | 0.34 |
| D        | 4.90       | —    | 5.40 |
| D1       | 4.80       | —    | 5.15 |
| D2       | 3.70       | —    | 4.20 |
| E        | 5.90       | —    | 6.50 |
| E1       | 5.65       | 5.80 | 5.95 |
| E2       | 3.32       | 3.50 | 3.63 |
| e        | 1.27BSC    |      |      |
| H        | 0.50       | —    | 0.93 |
| L        | 0.45       | —    | 0.91 |
| $\theta$ | 0°         | —    | 12°  |

## Marking Outline



Part Name: GMN02906LM

1. Logo Mark: 
2. P/N Mark: 02906LM
3. Date Code: XXXX
4. Pin 1#: ●

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